	(Test Item)	(Condition)	(Sample size)	(Decision)	(Reference)
1	高温反偏 (High Temperature Reverse Bias)	b、Time: 168h/1000h; c、Temperature: Fast Recovery Diode or Thyristor: 125℃; Discrete Device,MOSFET or IGBT: 145℃; Rectifier D icde: 150 ℃.	5PCS (FG)	LSL≤Electrical Parameter≤USL	IEC 60747
2	(High Temperature Grating Bias)	b、Temperature: c、Time: 168h/1000h.	5PCS (FG)	LSL≤Electrical Parameter≤USL	IEC 60747
3	温度循环 (Temperature Cycling)	a、Tempe Temperat b、Conve c、Cycle rature: Low Temperature -55℃ for 30min; High ure 150℃ for 30min; rsion Time: 10s; Times: 10Times/100Times.	5PCS (FG)	LSL≤Electrical Parameter≤USL	IEC 60068-2-14 Test Na
4	恒温恒湿 (Constant Temperature and Humidity)	a、Tempe b、Humid c、Time: rature: 85℃; ity: 85% RH; 168h/1000h.	5PCS (FG)	LSL≤Electrical Parameter≤USL	IEC 60068-2-67
[illegible]	功率循环	[illegible]	[illegible]	LSL≤Electrical Parameter≤USL	[illegible]
6	高温存储 (High Temperature Stora	a、Temperature: Tstgmax; b、Time: 168H/1000H.	5PCS (FG)	LSL≤Electrical Parameter≤USL	IEC 60068-2-2
[illegible]	低温存储	a、Temperature: Tstgmin b、Time: 168H/1000H	[illegible]	[illegible]	[illegible]
8	冲击试验 (Shock Test)	a、Max.: 50G; b、Pulse Time: 6ms, Sine Half Wave; c、Dir.: X / Y / Z, 3 Positive and 3 Negative Impacts, 18Times in total.	5PCS (FG)	LSL≤Electrical Parameter≤USL	IEC 60068-2-27 Test Ea
[illegible]	振动试验 (Vibration Test)	a、Vibration Waveform: 5~200 Hz, Sine Wave; c、Direction of Vibration: X, Y, Z per axis	5PCS (FG)	LSL≤Electrical Parameter≤USL	[illegible]